



01-11-02

2872

985401/23401
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Vladimir Voronkov et al. Art Unit 2812
Serial No. 09/972,608
Filed October 5, 2001
Confirmation No. 4591
For METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON

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INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

The Commissioner is hereby authorized to charge any fees incurred regarding this Information Disclosure Statement to Account No. 19-1345 if an Office Action was issued prior to the date of mailing of this Statement.

Please note that Applicants make no representation as to the accuracy or completeness of the translations submitted herewith.


Respectfully submitted,

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Application Number	09/972,608
Filing Date	October 5, 2001
Confirmation Number	4591
First Named Inventor	Vladimir Voronkov et al.
Group Art Unit	2812
Examiner Name	Unknown

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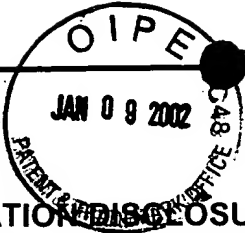
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985401/23401

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	1	4,314,595		Yamamoto et al.	02/09/1982
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	15	5,968,264		Iida et al.	10/19/1999
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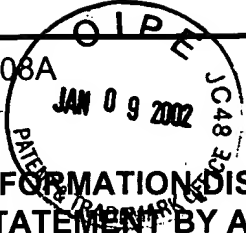
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
	22	EP	0 503 816	B1	Shin-Etsu Handotai Company Ltd.	09/16/1992	
	23	EP	0 504 837	A2	Shin-Etsu Handotai Company Ltd.	09/23/1992	
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	28	EP	0 909 840	A1	Shinetsu Handota KK	04/21/1999	

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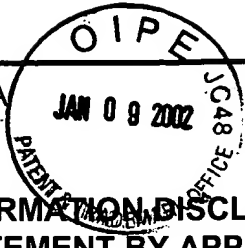
	29	EP	0 962 556	A1	Shin-Etsu Handotai Company Ltd.	12/08/1999	
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	47	PCT	WO 01/21861	A1	MEMC Electronic Materials Inc.	03/29/2001	
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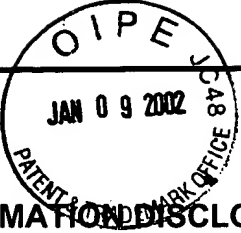
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	52	ABE, T., et al., "Behavior of Point Defects in FZ Silicon Crystals", Semiconductor Silicon 1990, <i>Proceedings of the Sixth International Symposium on Silicon Materials Science and Technology</i> , Vol. 90-7 (1990), pp. 105-116	
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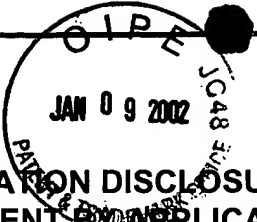
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